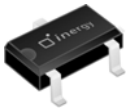
iM2323



N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☑ Surface-mounted package
- ☑ Advanced trench cell design
- ☑ Advanced trench cell design
- ☑ Advanced trench cell design

1.2 Applications

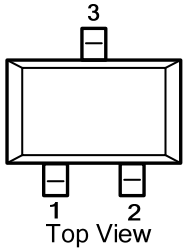
- ☑ Portable appliances
- ☑ High speed switch
- ☑ Battery management
- ☑ Low power DC to DC Converter

1.3 Quick reference

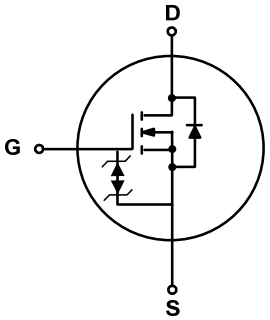
- ☑ BV ≧ 30 V
- ☑ P_{tot} ≦ 1 W
- ☑ I_D ≦ 5.6 A
- ☑ $R_{DS(ON)}$ ≦ 20 mΩ @ V_{GS} = 10 V
- ☑ $R_{DS(ON)}$ ≦ 31 mΩ @ V_{GS} = 4.5 V

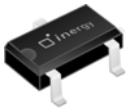
2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)		
2	Source(S)		
3	Drain(D)		



Top View
SOT23-3L





3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	T_A = 25 ℃	-	30	V
V_{GS}	Gate-Source Voltage	T_A = 25 ℃	-	± 20	V
I_D*	Drain Current	T_A = 25 ℃, V_{GS} = 10 V	-	5.6	A
I_{DM}*,**	Pulsed Drain Current	T_A = 25 ℃, V_{GS} = 10 V	-	22	A
P_{tot}*	Total Power Dissipation	T_A = 25 ℃	-	1	W
T_{stg}	Storage Temperature		- 55	150	℃
T_J	Junction Temperature		- 55	150	℃
I_S	Diode Forward Current	T_A = 25 ℃	-	5.6	A
$R_{\theta JA}$*	Thermal Resistance- Junction to Ambient		-	125	℃ / W

Notes :

* Surface Mounted on 1 in^2 pad area, t ≤ 10 sec

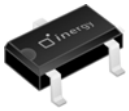
** Pulse width ≤ 300 μs, duty cycle ≤ 2 %

4. Marking Information

Product Name	Marking
iM2323	323XX X : Date Code

5. Ordering Code

iM2323



6. Electrical Characteristics (T_A = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_{DS} = 250 µA	30	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = 0 V, I_{DS} = 250 µA	1	-	2.5	V
I_{DSS}	Drain Leakage Current	V_{DS} = 24 V, V_{GS} = 0 V	-	-	1	µA
I_{GSS}	Gate Leakage Current	V_{GS} = 0 V, V_{GS} = ± 20 V	-	-	± 10	uA
$R_{DS(ON)}$[a]	On-State Resistance	V_{GS} = 10 V, I_{DS} = 5 A	-	16	20	mΩ
		V_{GS} = 4.5 V, I_{DS} = 3 A	-	24	31	
Diode Characteristics						
V_{SD}[a]	Diode Forward Voltage	I_{SD} = 5 A, V_{GS} = 0 V	-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_{DS} = 5 A, V_{GS} = 0 V dI_{SD}/dt = 100 A/µs	-	7	-	nS
Q_{rr}	Reverse Recovery Charge		-	3	-	nC
Dynamic Characteristics[b]						
C_{iss}	Input Capacitance	V_{GS} = 0 V, V_{DS} = 15 V Frequency = 1 MHz	-	862	-	pF
C_{oss}	Output Capacitance		-	80	-	
C_{rss}	Reverse Transfer Capacitance		-	68	-	
t_d(on)	Turn-on Delay Time	V_{DS} = 15 V, V_{GEN} = 10 V, R_G = 3.9 Ω, R_L = 3 Ω, I_{DS} = 5 A	-	5	-	nS
t_r	Turn-on Rise Time		-	16	-	
t_d(off)	Turn-off Delay Time		-	23	-	
t_f	Turn-off Fall Time		-	14	-	
Gate Charge Characteristics[b]						
Q_g	Total Gate Charge	V_{DS} = 15 V, V_{GS} = 10 V, I_{DS} = 5 A	-	16	-	nC
Q_{gs}	Gate-Source Charge		-	4	-	
Q_{gd}	Gate-Drain Charge		-	2.2	-	

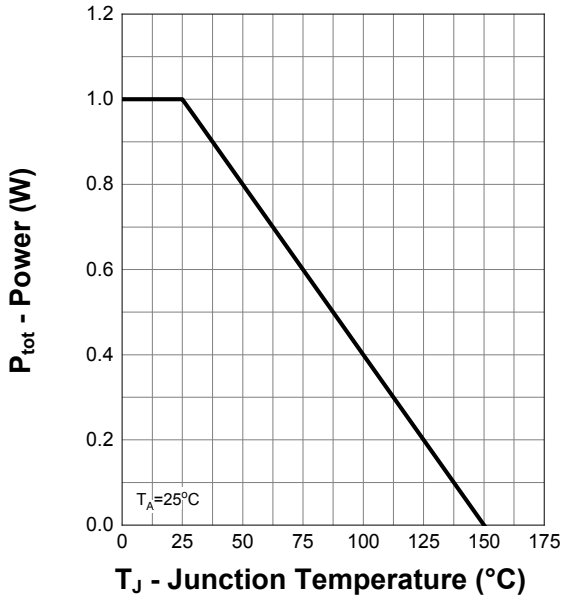
Notes :

a : Pulse test ; pulse width ≤ 300 µs, duty cycle ≤ 2%

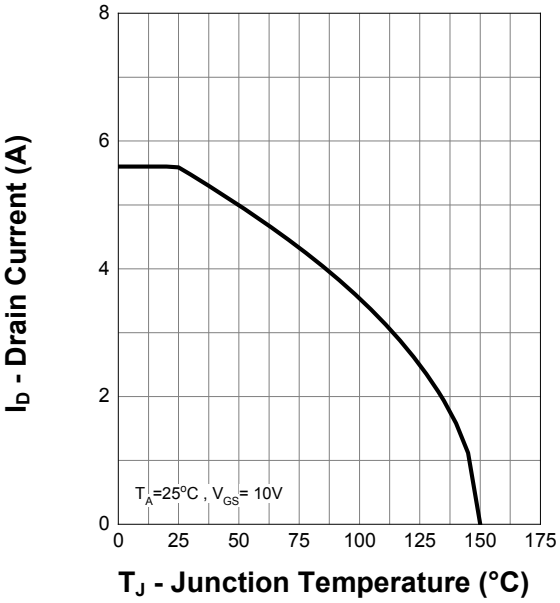
b : Guaranteed by design, not subject to production testing

7. Typical Characteristics

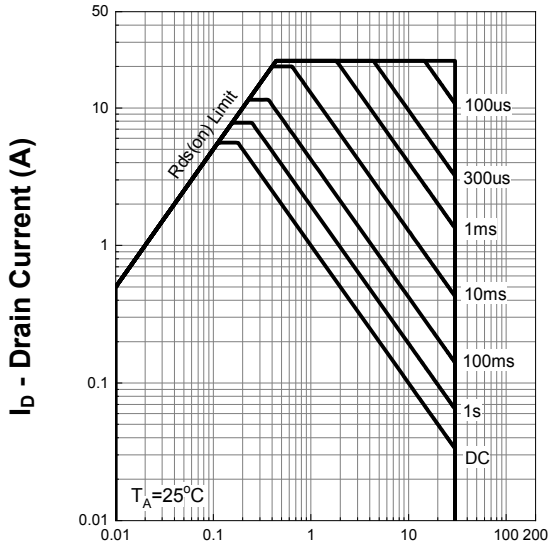
Power Capability



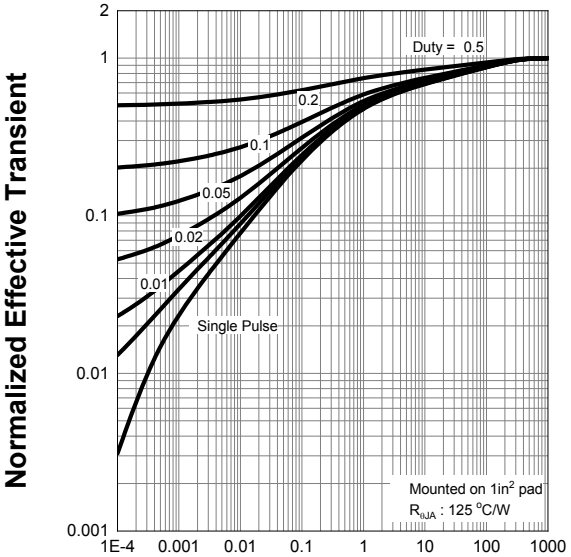
Current Capability



Safe Operating Area

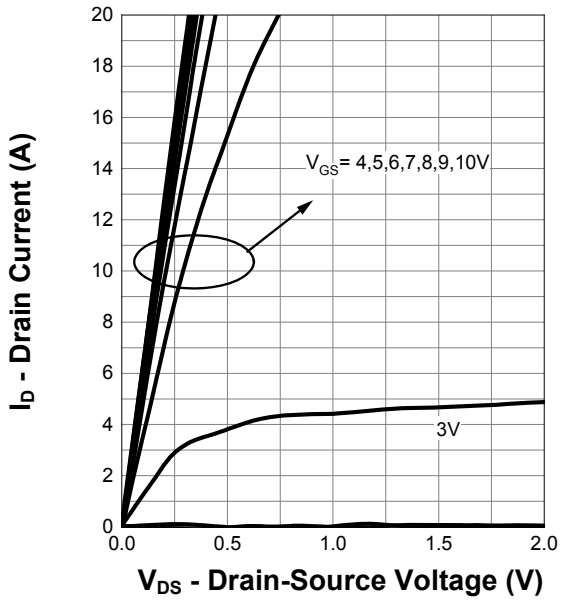


Transient Thermal Impedance

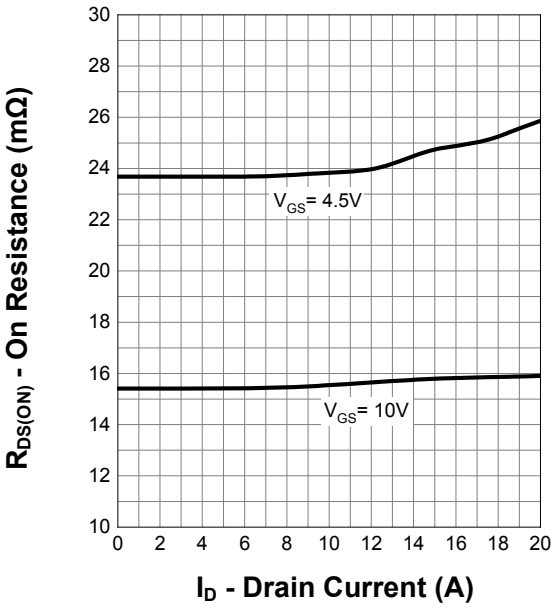


7. Typical Characteristics (cont.)

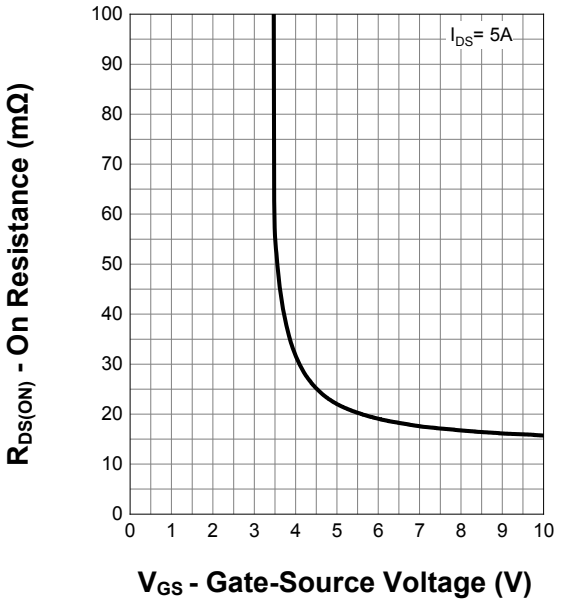
Output Characteristics



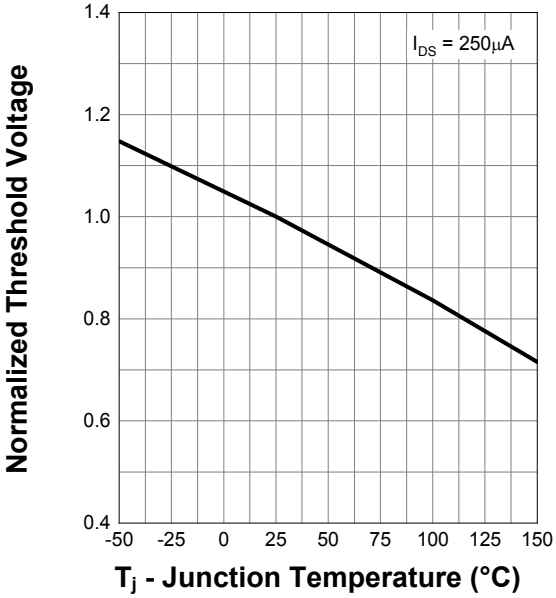
On Resistance



Transfer Characteristics

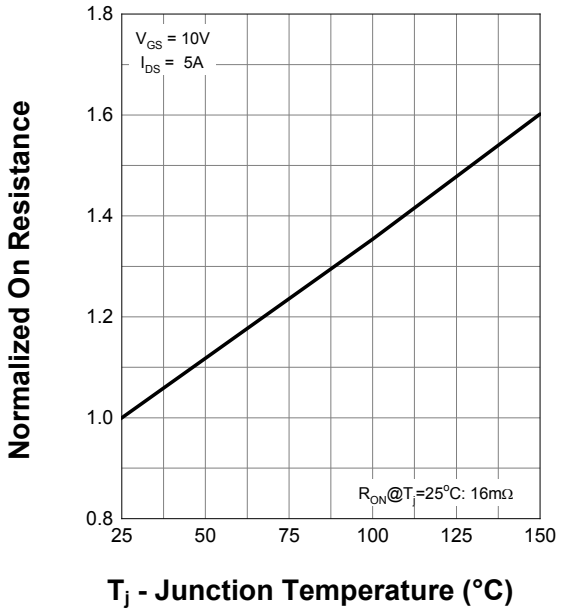


Normalized Threshold Voltage

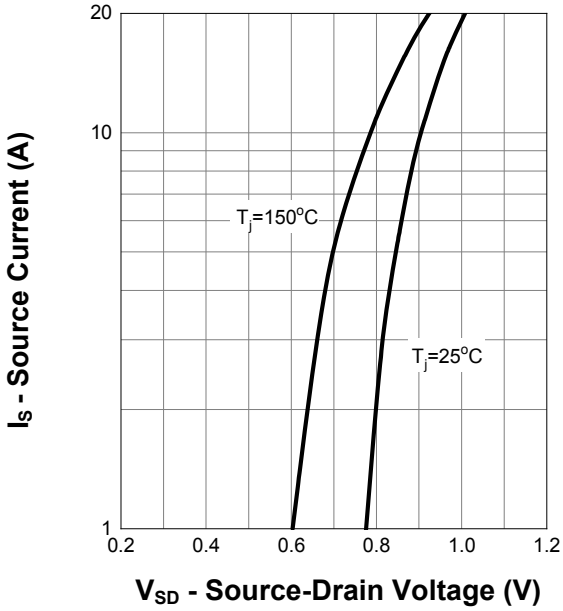


7. Typical Characteristics (cont.)

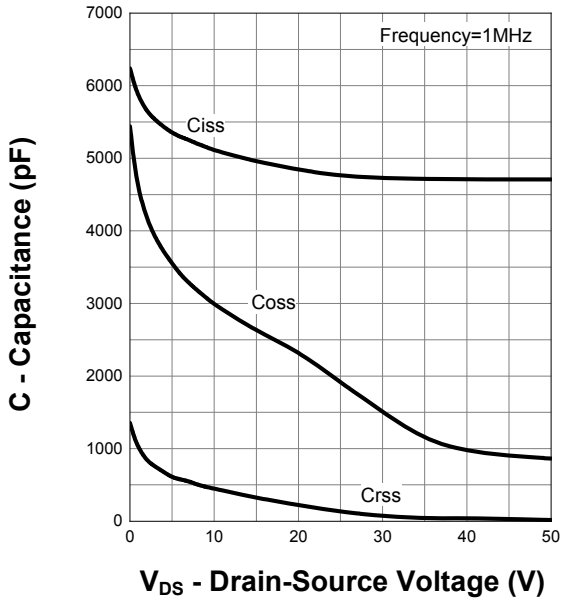
Normalized On Resistance



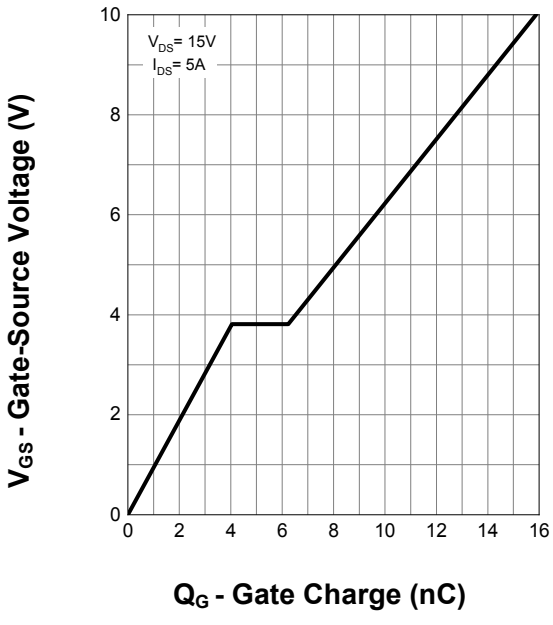
Diode Forward Current



Capacitance

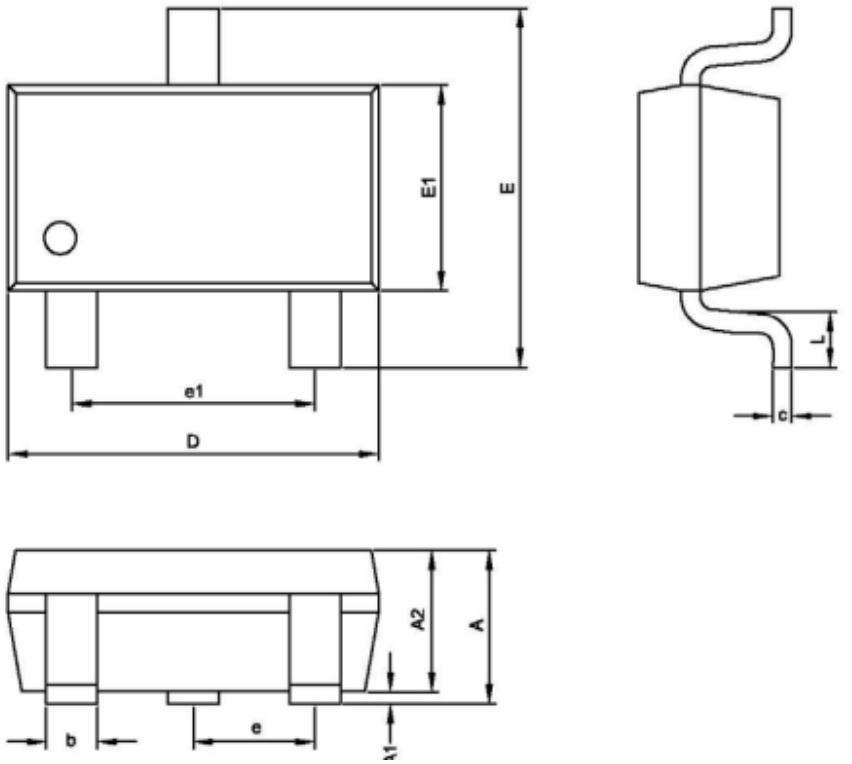


Gate Charge



8. Package Dimensions

SOT23-3L



SYMBOL	Dimension in mm	
	MIN.	MAX.
A	1.00	1.45
A1	0	0.15
A2	1.00	1.30
D	2.70	3.10
E	2.60	3.00
E1	1.50	1.75
c	0.08	0.25
b	0.30	0.50
e	0.95 BCS	
e1	1.9 BCS	
L	0.30	0.60